## Recitation 8 EE 3161 – Spring 2008

1) In the following two diagrams, are the BJTs shown biased in Forward Active, Inverse Active, Saturation, or Cutoff?

Sketch your own plot of log(n,p) vs. x for the case of an npn transistor in saturation.



2) For the silicon p<sup>+</sup>np bipolar transistor shown below, what are α<sub>T</sub>, γ, and β if we do not include base recombination and the device is biased in forward active? What if the device is biased in inverse active? (Ignore depletion region chances when using W for inverse active.) Why are the numbers so different?



$$p^{+}: N_{a} = 5 \times 10^{17} \text{ cm}^{-3}$$
  
n:  $N_{d} = 3 \times 10^{16} \text{ cm}^{-3}$   
p:  $N_{a} = 6 \times 10^{15} \text{ cm}^{-3}$   
 $\tau_{E} = \tau_{B} = 0.2 \mu \text{s}; \tau_{C} = 1 \mu \text{s}$   
 $A = 1 \text{ cm}^{2}$   
 $V_{EB} = 0.3 \text{V}$   
 $V_{CB} = -3 \text{V}$